



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

**FUKUDA, Masatoshi et al.**

Serial No.: 10/020,951

Filed: **December 19, 2001**

For: **SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

Group Art Unit: 2815

Examiner: **LANDAU, M.**

P.T.O. Confirmation No.: 8648

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231

January 28, 2003

Sir:

In response to the Office Action dated October 1, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please **CANCEL** claims 5 and 6 without prejudice or disclaimer.

Please **AMEND** claims as follows:

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- sub B11*  
*a1*
1. (Amended) A semiconductor device comprising:  
a capacitor formed above a semiconductor substrate and including  
a cylindrical-shaped storage electrode,  
a capacitor dielectric film formed on the storage electrode, and  
a plate electrode formed on the capacitor dielectric film,